# OptiMOS™3 M-Series Power-MOSFET

Features

• Dual N-channel

• Optimized for 5V driver application (Notebook, VGA, POL)

• Low FOM_{SW} for High Frequency SMPS

• 100% Avalanche tested

• Very low on-resistance $R_{DS(on)}$ @ V_{GS}=4.5 V

• Excellent gate charge x $R_{DS(on)}$ product (FOM)

• Qualified for consumer level application

• Pb-free plating; RoHS compliant

• Halogen-free according to IEC61249-2-21

Product Summary

V_{DS}		30	V
$R_{DS(on),max}$	V_{GS}=10 V	22	mΩ
	V_{GS}=4.5 V	27	
I_D		7.7	A

PG-DSO-8

Type	Package	Marking
BSO220N03MD G	PG-DSO-8	220N03MD
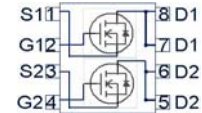
Maximum ratings, at T_j=25 °C, unless otherwise specified

Parameter	Symbol	Conditions	Value		Unit
			10 secs	**steady state**	
Continuous drain current[1]	I_D	V_{GS}=10 V, T_A=25 °C	7.7	6	A
		V_{GS}=10 V, T_A=90 °C	5.3	4.4	
		V_{GS}=4.5 V, T_A=25 °C	6.9	5.8	
		V_{GS}=4.5 V, T_A=90 °C	4.8	4	
Pulsed drain current[2]	$I_{D,pulse}$	T_A=25 °C	54		
Avalanche current, single pulse[3]	I_{AS}	T_A=25 °C	7.7		
Avalanche energy, single pulse	E_{AS}	I_D=7.7 A, R_{GS}=25 Ω	9		mJ
Gate source voltage	V_{GS}		±20		V
Power dissipation[1]	P_{tot}	T_A=25 °C	2	1.4	W
Operating and storage temperature	T_j, T_{stg}		-55 ... 150		°C
IEC climatic category; DIN IEC 68-1			55/150/56		

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Thermal characteristics

Parameter	Symbol	Conditions	min.	typ.	max.	Unit
Thermal resistance, junction - soldering point	R_{thJS}		-	-	50	K/W
Thermal resistance, junction - ambient	R_{thJA}	minimal footprint, $t_p \leq 10$ s	-	-	110	
		minimal footprint, steady state	-	-	150	
		6 cm^2 cooling area[1], $t_p \leq 10$ s	-	-	62.5	
		6 cm^2 cooling area[1], steady state	-	-	90	

Electrical characteristics, at T_j=25 °C, unless otherwise specified

Static characteristics

Parameter	Symbol	Conditions	min.	typ.	max.	Unit
Drain-source breakdown voltage	$V_{(BR)DSS}$	V_{GS}=0 V, I_D=1 mA	30	-	-	V
Gate threshold voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=250 µA	1	-	2.1	
Zero gate voltage drain current	I_{DSS}	V_{DS}=30 V, V_{GS}=0 V, T_j=25 °C	-	0.1	10	µA
		V_{DS}=30 V, V_{GS}=0 V, T_j=125 °C	-	10	100	
Gate-source leakage current	I_{GSS}	V_{GS}=16 V, V_{DS}=0 V	-	10	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	V_{GS}=4.5 V, I_D=6.9 A	-	21.6	27	mΩ
		V_{GS}=10 V, I_D=7.7 A	-	18.3	22	
Gate resistance	R_G		0.6	1.3	2.3	Ω
Transconductance	g_{fs}	$\|V_{DS}\|>2\|I_D\|R_{DS(on)max}$, I_D=7.7 A	9	18	-	S

[1] Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm2 (one layer, 70 µm thick) copper area for drain connection. PCB is vertical in still air. One transistor active.

[2] See figure 3 for more detailed information

[3] See figure 13 for more detailed information

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Dynamic characteristics

Parameter	Symbol	Conditions	min.	typ.	max.	Unit
Input capacitance	C_{iss}	V_{GS}=0 V, V_{DS}=15 V, f=1 MHz	-	600	800	pF
Output capacitance	C_{oss}		-	230	310	
Reverse transfer capacitance	C_{rss}		-	12	-	
Turn-on delay time	$t_{d(on)}$	V_{DD}=15 V, V_{GS}=4.5 V, I_D=7.7 A, R_G=1.6 Ω	-	5.7	-	ns
Rise time	t_r		-	2.8	-	
Turn-off delay time	$t_{d(off)}$		-	6.4	-	
Fall time	t_f		-	3.4	-	

Gate Charge Characteristics[4]

Parameter	Symbol	Conditions	min.	typ.	max.	Unit
Gate to source charge	Q_{gs}	V_{DD}=15 V, I_D=7.7 A, V_{GS}=0 to 4.5 V	-	1.8	-	nC
Gate charge at threshold	$Q_{g(th)}$		-	1.0	-	
Gate to drain charge	Q_{gd}		-	0.9	-	
Switching charge	Q_{sw}		-	1.7	-	
Gate charge total	Q_g		-	3.8	5	
Gate plateau voltage	$V_{plateau}$		-	3.0	-	V
Gate charge total	Q_g	V_{DD}=15 V, I_D=7.7 A, V_{GS}=0 to 10 V	-	7.8	10	nC
Gate charge total, sync. FET	$Q_{g(sync)}$	V_{DS}=0.1 V, V_{GS}=0 to 4.5 V	-	3.3	4.4	
Output charge	Q_{oss}	V_{DD}=15 V, V_{GS}=0 V	-	6.1	8.1	

Reverse Diode

Parameter	Symbol	Conditions	min.	typ.	max.	Unit
Diode continuous forward current	I_S	T_A=25 °C	-	-	2.4	A
Diode pulse current	$I_{S,pulse}$		-	-	54	
Diode forward voltage	V_{SD}	V_{GS}=0 V, I_F=7.7 A, T_j=25 °C	-	0.88	1.1	V
Reverse recovery charge	Q_{rr}	V_R=15 V, I_F=I_S, di_F/dt=400 A/µs	-		10	nC

[4] See figure 16 for gate charge parameter definition

1 Power dissipation

P_{tot}=f(T_A); t_p≤10 s
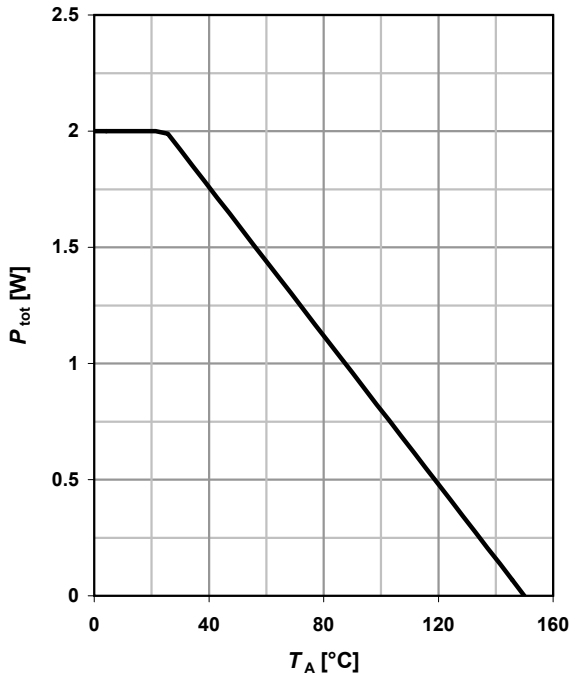
2 Drain current

I_D=f(T_A); t_p≤10 s

parameter: V_{GS}
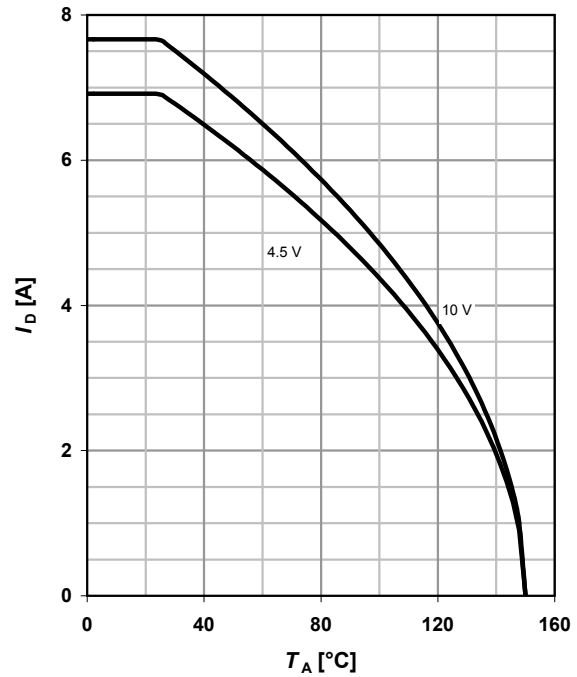
3 Safe operating area
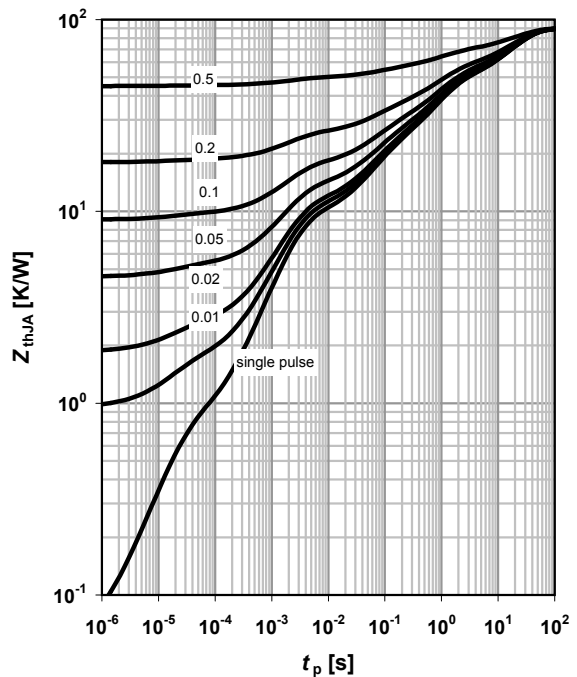
I_D=f(V_{DS}); T_A=25 °C[2]; D=0

parameter: t_p
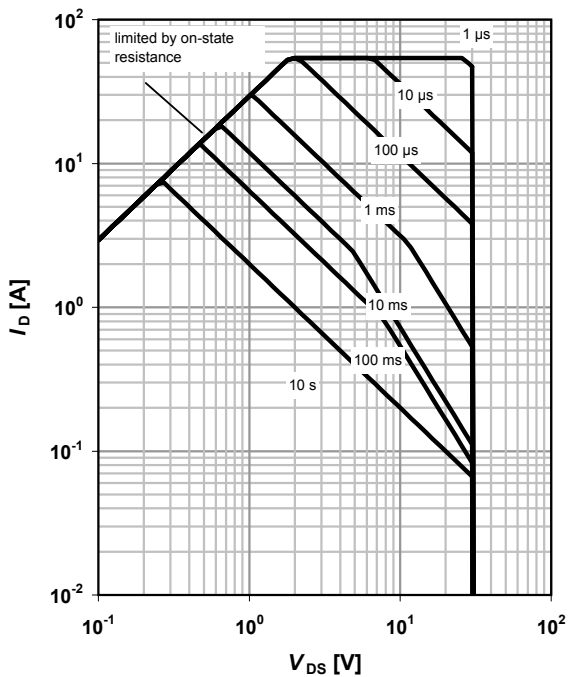
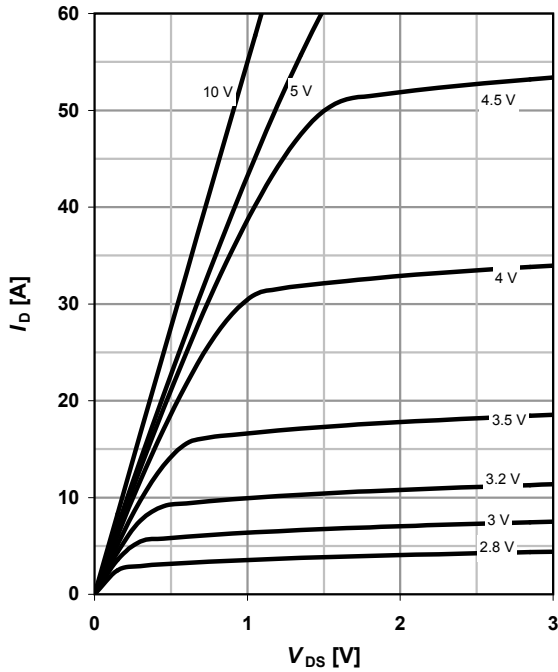**4 Max. transient thermal impedance**

Z_{thJA}=f(t_p)[2]

parameter: D=t_p/T

5 Typ. output characteristics

I_D=f(V_{DS}); T_j=25 °C

parameter: V_{GS}

6 Typ. drain-source on resistance

$R_{DS(on)}$=f(I_D); T_j=25 °C

parameter: V_{GS}
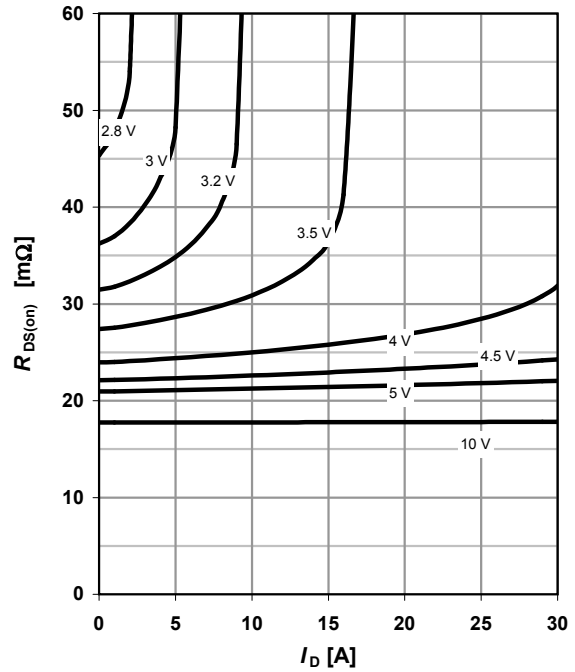
7 Typ. transfer characteristics

I_D=f(V_{GS}); $|V_{DS}|$>2$|I_D|R_{DS(on)max}$

parameter: T_j
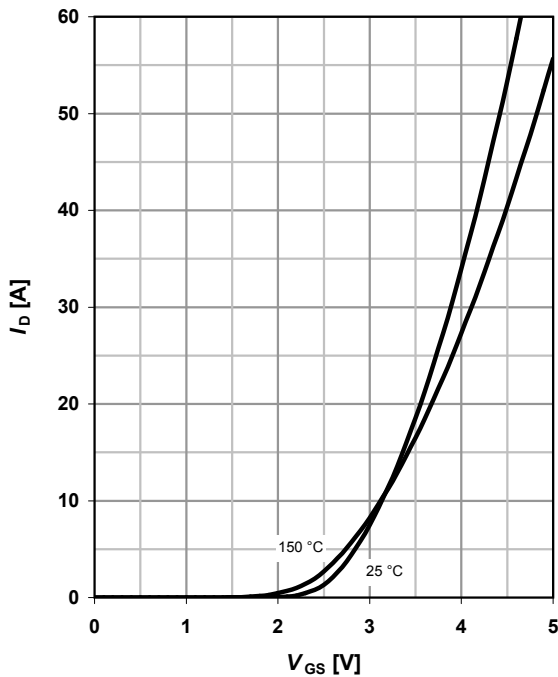
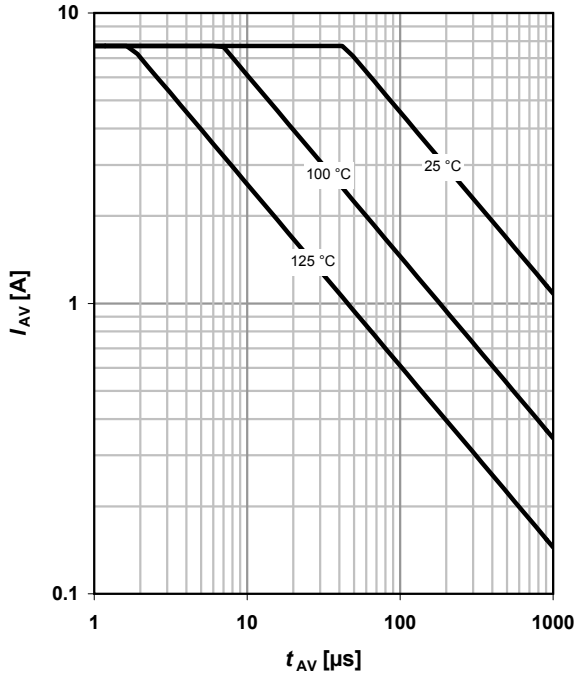**8 Typ. forward transconductance**

g_{fs}=f(I_D); T_j=25 °C
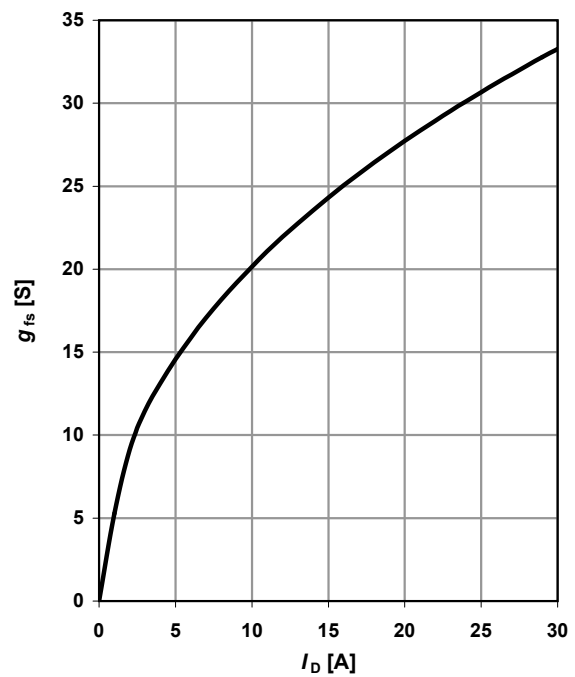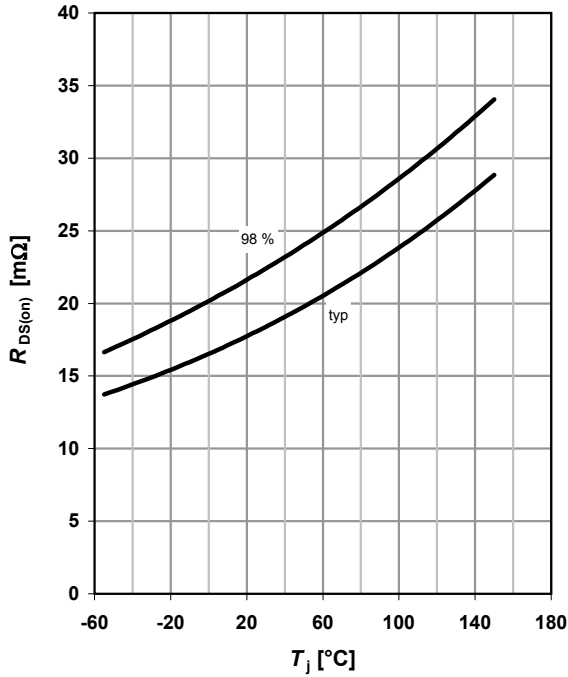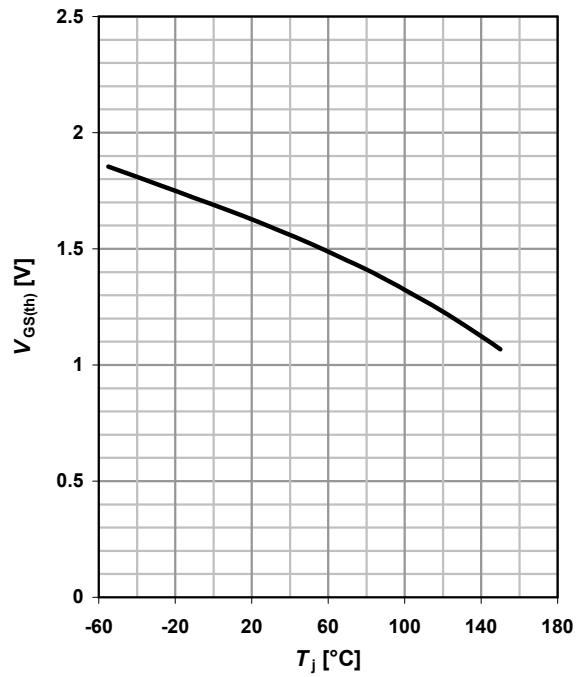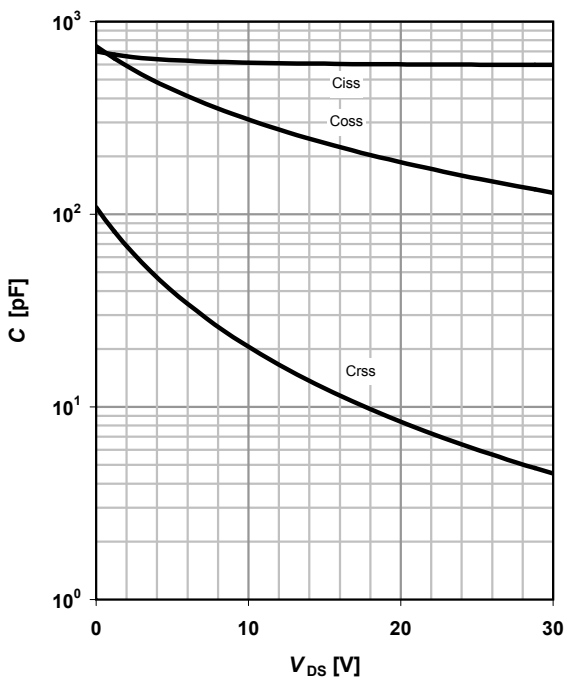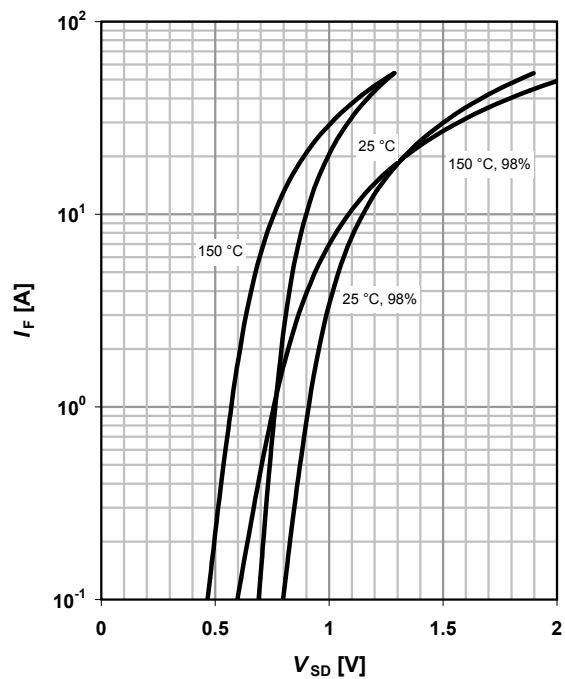
13 Avalanche characteristics
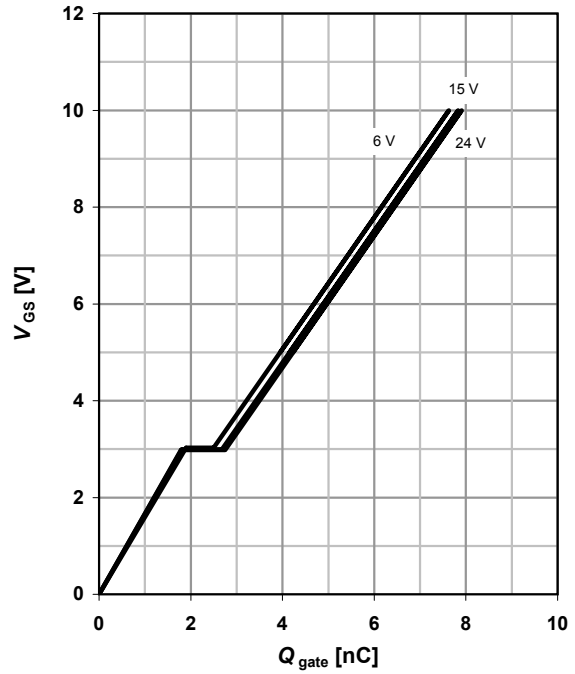
I_{AS}=f(t_{AV}); R_{GS}=25 Ω

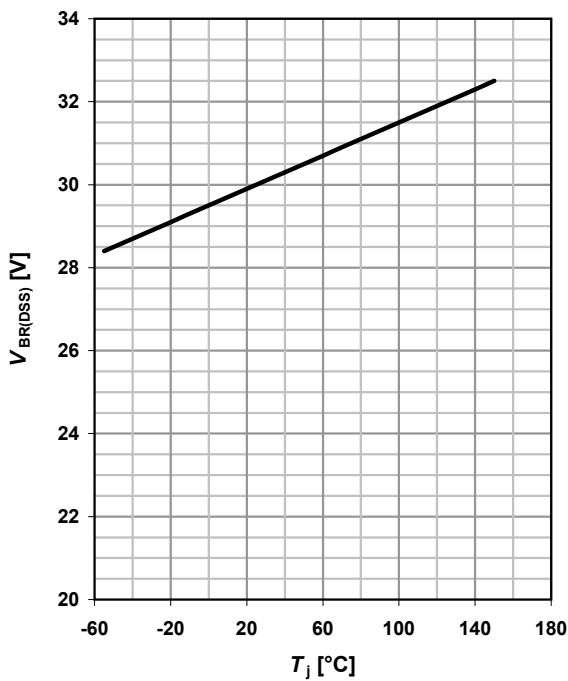parameter: $T_{j(start)}$

14 Typ. gate charge

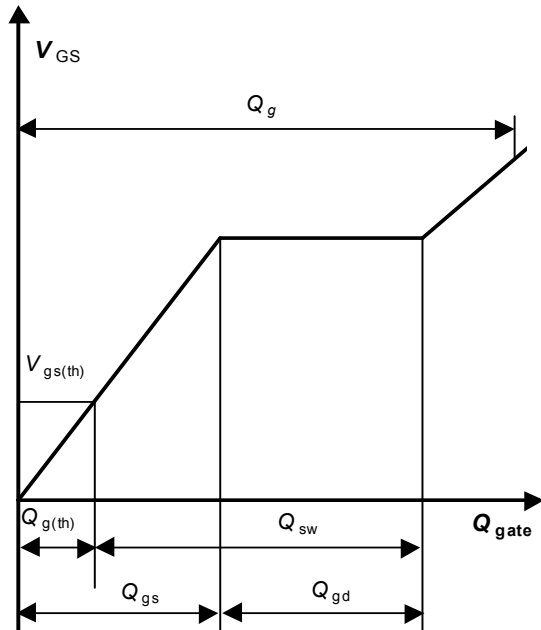V_{GS}=f(Q_{gate}); I_D=7.7 A pulsed

parameter: V_{DD}

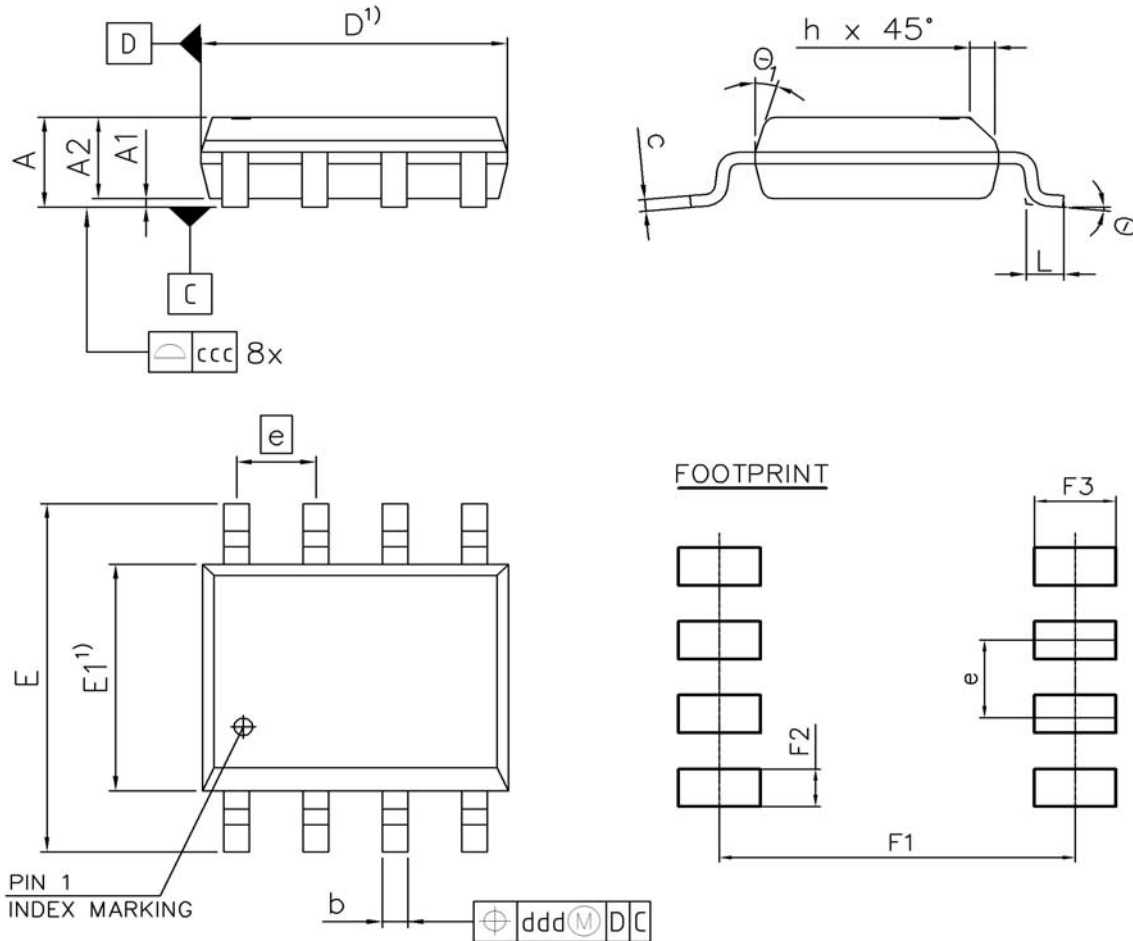## 15 Drain-source breakdown voltage

$V_{BR(DSS)}$=f(T_j); I_D=1 mA

16 Gate charge waveforms

Package Outline

PG-DSO-8: Outline

1) DOES NOT INCLUDE MOLD FLASH OR PROTRUSIONS.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	-	1.75	-	0.069
A1	0.10	-	0.004	-
A2	1.25	1.65	0.049	0.065
b	0.35	0.51	0.014	0.020
c	0.17	0.25	0.007	0.010
D	4.80	5.00	0.189	0.197
E	5.80	6.20	0.228	0.244
E1	3.80	4.00	0.150	0.157
e	1.27		0.050	
N	8		8	
L	0.39	0.89	0.015	0.035
h	0.23	0.50	0.009	0.020
Θ	0°	8°	0°	8°
Θ_1	-	19°	-	19°
ccc	0.10		0.004	
ddd	0.25		0.010	
F1	5.59	5.79	0.220	0.228
F2	0.55	0.75	0.022	0.030
F3	1.21	1.41	0.048	0.056

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